

### Features

- APD with 0.2 mm<sup>2</sup> active area
- 500 μm diameter active area
- High gain at low bias voltage
- Fast rise time, low capacitance
- Optimum gain: 50-60

### Description

Circular active area APD chip with 500μm diameter. Ceramic carrier type non hermetic SMD package with filter window (BP-Filter for 635nm). Reflow solderable.

### Application

- Laser range finder
- High speed photometry
- High speed optical communications
- Medical equipment

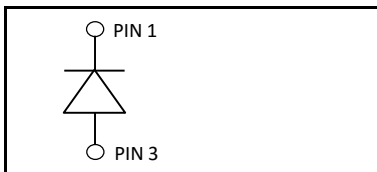
### RoHS

2011/65/EU

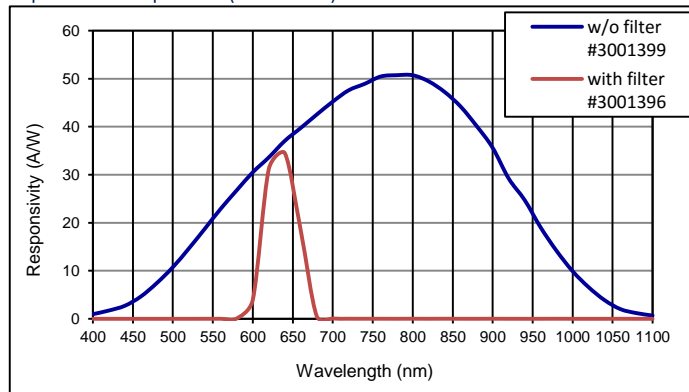
### Absolute maximum ratings

| Symbol            | Parameter                     | Min | Max  | Unit |
|-------------------|-------------------------------|-----|------|------|
| T <sub>STG</sub>  | Storage temp                  | -40 | 100  | °C   |
| T <sub>OP</sub>   | Operating temp                | -20 | 70   | °C   |
| M <sub>max</sub>  | Gain (I <sub>PO</sub> = 1 nA) | 200 |      |      |
| I <sub>PEAK</sub> | Peak DC current               |     | 0.25 | mA   |

### Schematic



### Spectral response (M = 100)

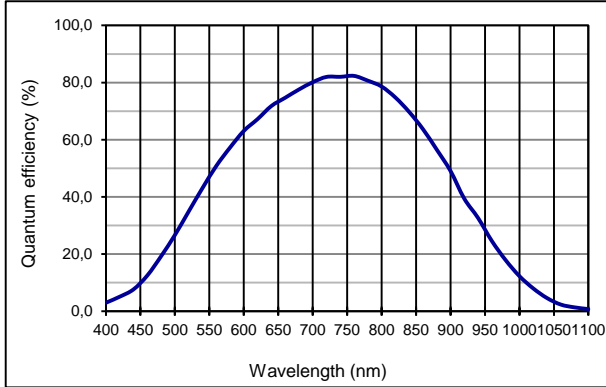


### Electro-optical characteristics @ 23 °C

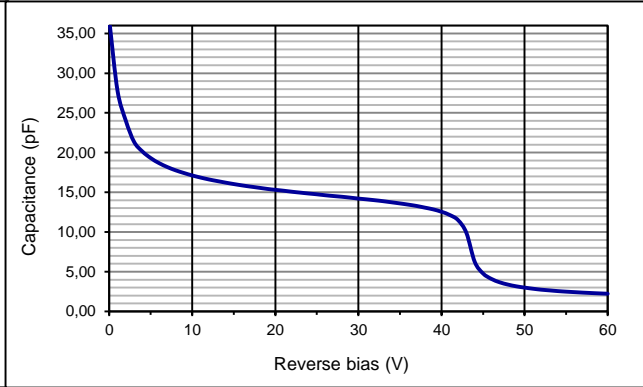
| Symbol          | Characteristic          | Test Condition                             | Min          | Typ  | Max | Unit            |
|-----------------|-------------------------|--|--------------|------|-----|-----------------|
|                 | Active area             |  | diameter 500 |      |     | μm              |
|                 | Active area             |  | 0.196        |      |     | mm <sup>2</sup> |
| I <sub>D</sub>  | Dark current            | M = 100                                    |              | 0.5  | 1.0 | nA              |
| C               | Capacitance             | M = 100                                    |              | 2.2  |     | pF              |
|                 | Responsivity            | M = 100; λ = 635 nm                        | 30           | 32   |     | A/W             |
| t <sub>R</sub>  | Rise time               | M = 100; λ = 905 nm; R <sub>L</sub> = 50 Ω |              | 0.35 |     | ns              |
|                 | Cut-off frequency       | -3dB                                       |              | 1    |     | GHz             |
| V <sub>BR</sub> | Breakdown voltage       | I <sub>R</sub> = 2 μA                      | 80           |      | 120 | V               |
|                 | Temperature coefficient | Change of V <sub>BR</sub> with temperature |              | 0.45 |     | V/K             |
|                 | Excess noise factor     | M = 100                                    |              | 2.2  |     |                 |
|                 | Excess noise index      | M = 100                                    |              | 0.2  |     |                 |



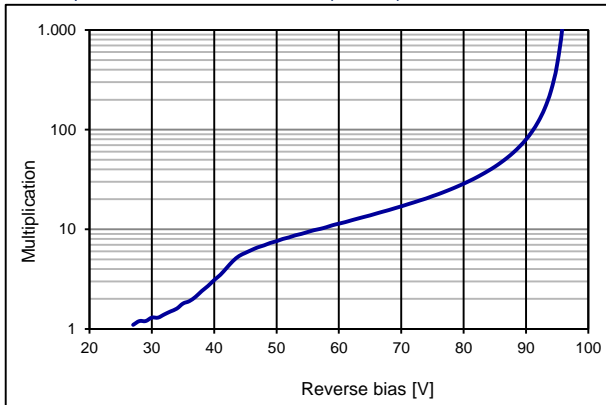
Quantum efficiency (23 °C)



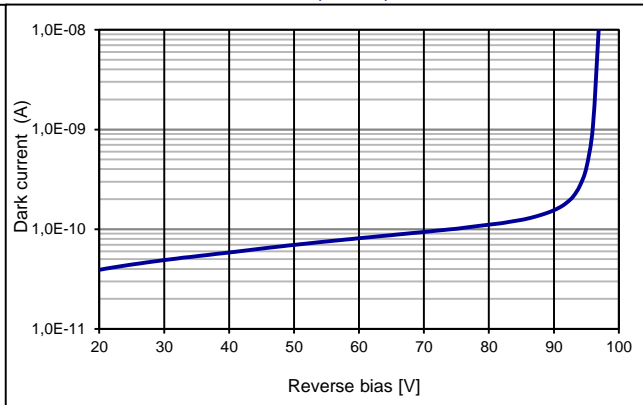
Capacitance as fct of reverse bias (23 °C)



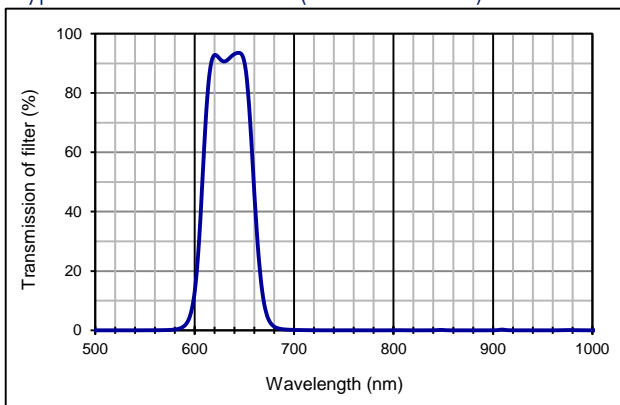
Multiplication as fct of bias (23 °C)



Dark current as fct of bias (23 °C)

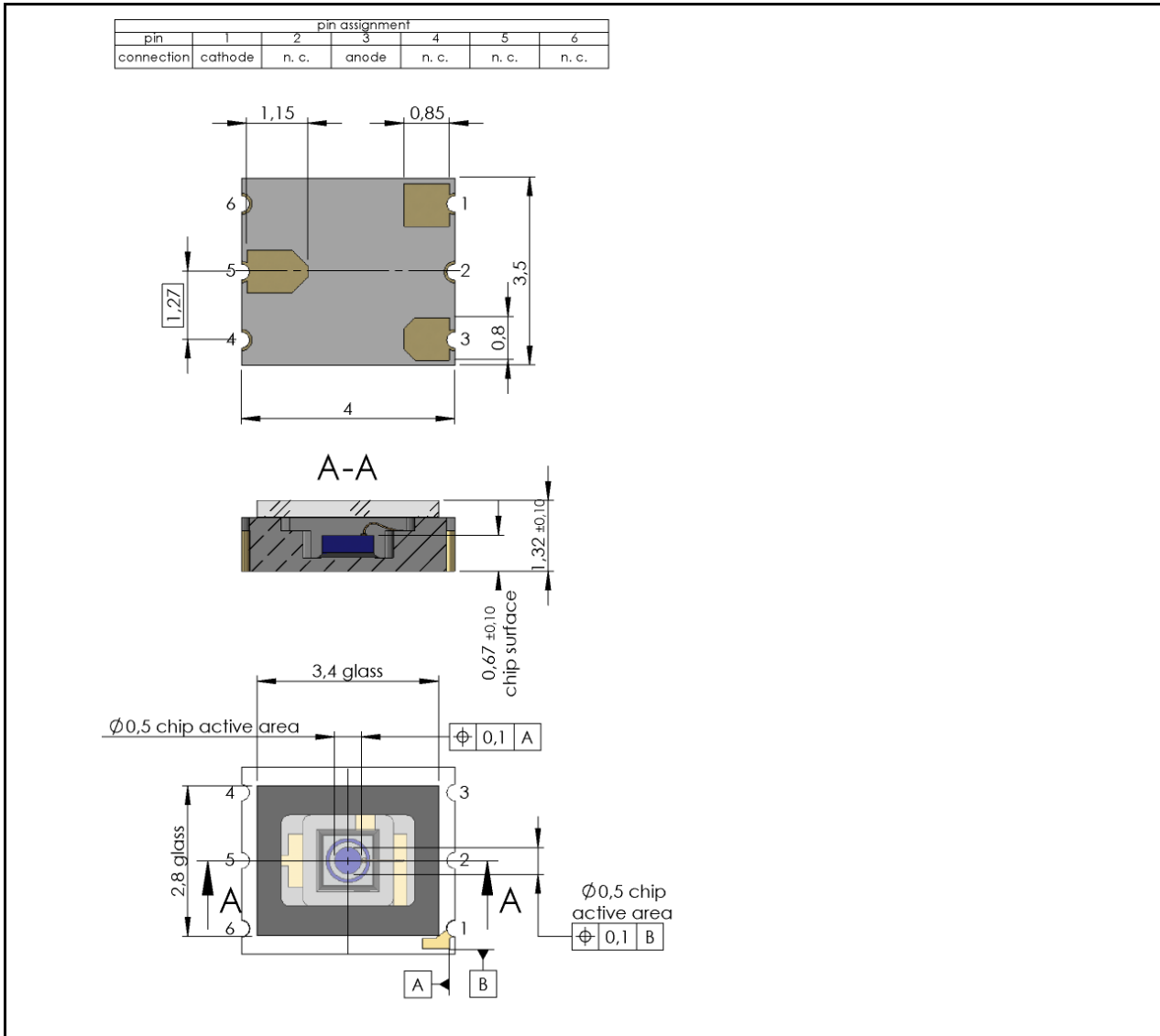


Typ. filter characteristics (center 635 nm)

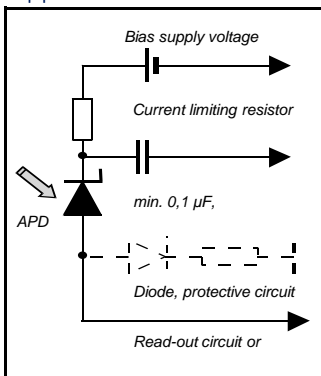


full filter specification upon request

Technical Drawing, Package: LCC6.1



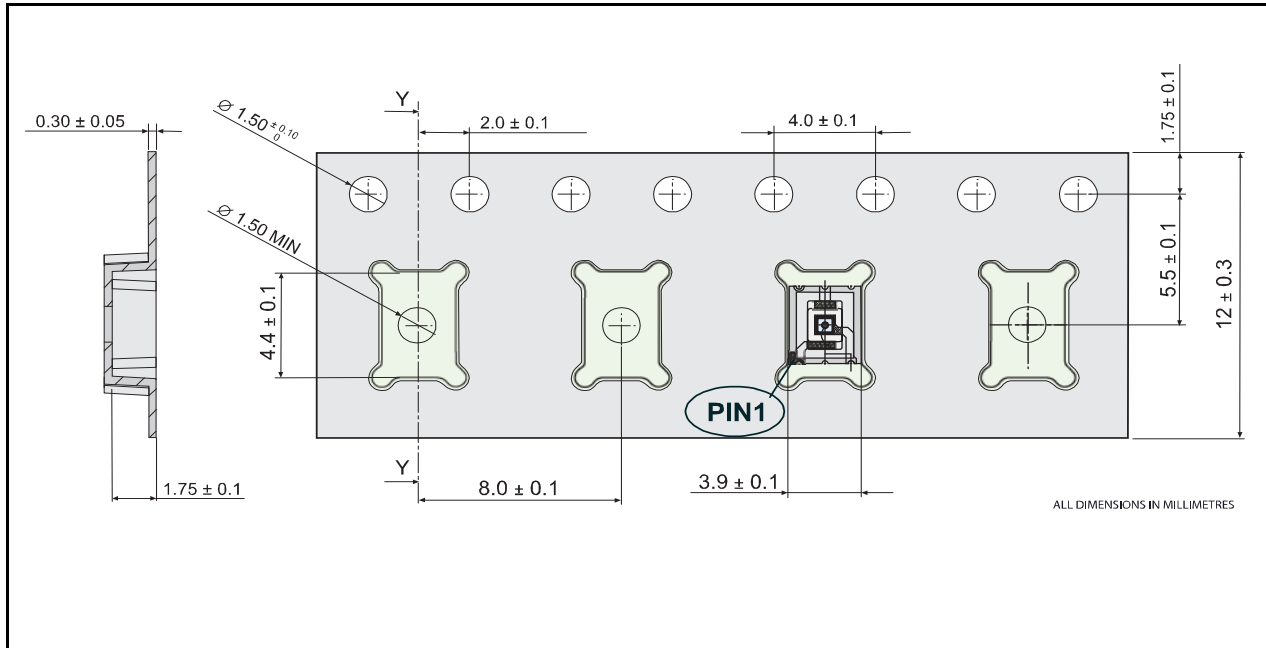
Application hints:



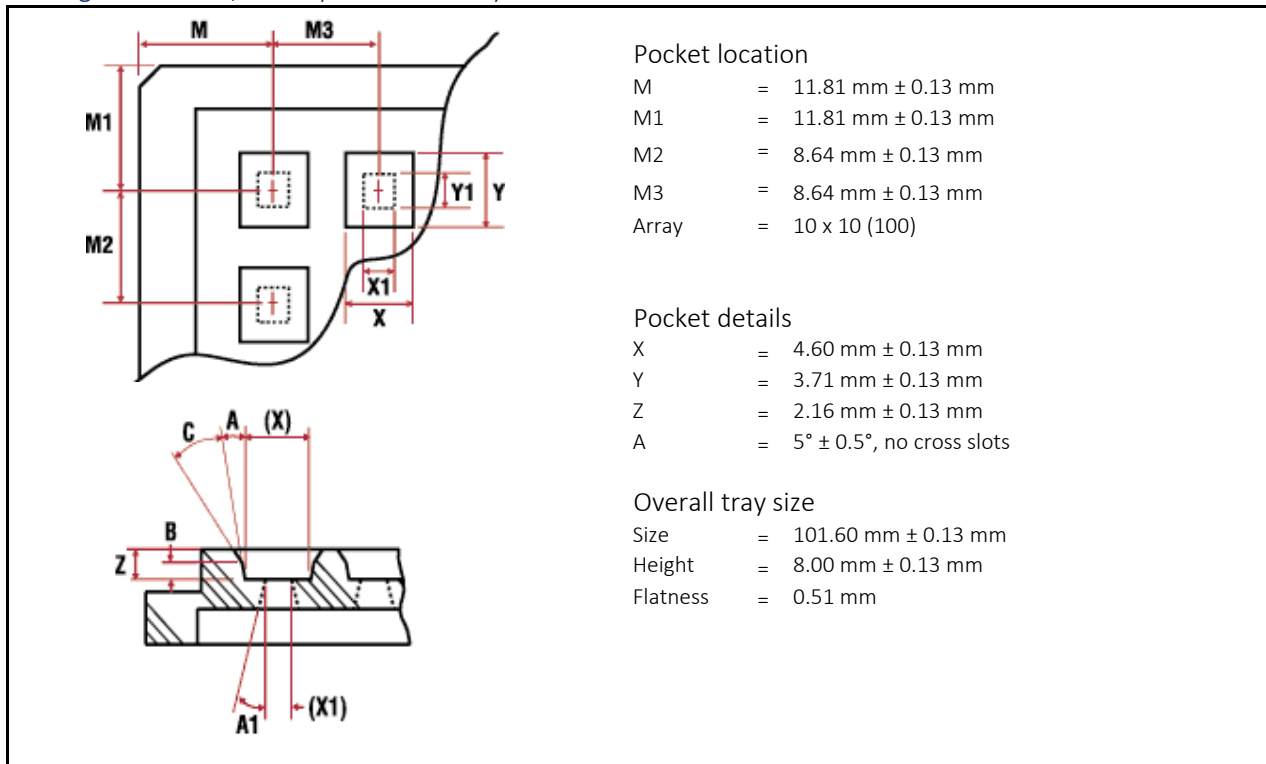
- Current should be limited by a protecting resistor or current limiting - IC inside the power supply
- For low light level applications blocking of ambient light should be used
- For high gain applications bias voltage should be temperature compensated
- Please consider basic ESD protection while handling
- Use low noise read-out - IC
- For further questions please refer to document "Instructions for handling and processing"
- Optimum gain: 50-60



Package dimension, large quantities on reel



Package dimension, small quantities in trays



Disclaimer: Due to our strive for continuous improvement, specifications are subject to change within our PCN policy according to JESD46C.